

# XN0121E (XN121E)

## Silicon NPN epitaxial planar type

For switching/digital circuits

### ■ Features

- Two elements incorporated into one package  
(Emitter-coupled transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

### ■ Basic Part Number

- UNR221E (UN221E) × 2

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter                             | Symbol           | Rating      | Unit             |
|---------------------------------------|------------------|-------------|------------------|
| Collector-base voltage (Emitter open) | $V_{\text{CBO}}$ | 50          | V                |
| Collector-emitter voltage (Base open) | $V_{\text{CEO}}$ | 50          | V                |
| Collector current                     | $I_{\text{C}}$   | 100         | mA               |
| Total power dissipation               | $P_{\text{T}}$   | 300         | mW               |
| Junction temperature                  | $T_{\text{j}}$   | 150         | $^\circ\text{C}$ |
| Storage temperature                   | $T_{\text{stg}}$ | -55 to +150 | $^\circ\text{C}$ |

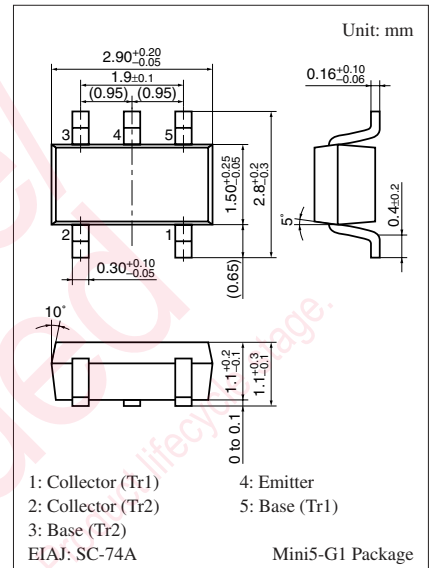
### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter                                    | Symbol                                     | Conditions  | Min  | Typ  | Max  | Unit             |
|--|--|---|------|------|------|------------------|
| Collector-base voltage (Emitter open)        | $V_{\text{CBO}}$                           | $I_{\text{C}} = 10 \mu\text{A}$ , $I_{\text{E}} = 0$  | 50   |      |      | V                |
| Collector-emitter voltage (Base open)        | $V_{\text{CEO}}$                           | $I_{\text{C}} = 2 \text{ mA}$ , $I_{\text{B}} = 0$  | 50   |      |      | V                |
| Collector-base cutoff current (Emitter open) | $I_{\text{CBO}}$                           | $V_{\text{CB}} = 50 \text{ V}$ , $I_{\text{E}} = 0$   |      |      | 0.1  | $\mu\text{A}$    |
| Collector-emitter cutoff current (Base open) | $I_{\text{CEO}}$                           | $V_{\text{CE}} = 50 \text{ V}$ , $I_{\text{B}} = 0$   |      |      | 0.5  | $\mu\text{A}$    |
| Emitter-base cutoff current (Collector open) | $I_{\text{EBO}}$                           | $V_{\text{EB}} = 6 \text{ V}$ , $I_{\text{C}} = 0$  |      |      | 0.2  | mA               |
| Forward current transfer ratio               | $h_{\text{FE}}$                            | $V_{\text{CE}} = 10 \text{ V}$ , $I_{\text{C}} = 5 \text{ mA}$                                      | 60   |      |      | —                |
| $h_{\text{FE}}$ Ratio *                      | $h_{\text{FE}}(\text{Small}/\text{Large})$ | $V_{\text{CE}} = 10 \text{ V}$ , $I_{\text{C}} = 5 \text{ mA}$                                      | 0.50 | 0.99 |      | —                |
| Collector-emitter saturation voltage         | $V_{\text{CE(sat)}}$                       | $I_{\text{C}} = 10 \text{ mA}$ , $I_{\text{B}} = 0.3 \text{ mA}$                                    |      |      | 0.25 | V                |
| Output voltage high-level                    | $V_{\text{OH}}$                            | $V_{\text{CC}} = 5 \text{ V}$ , $V_{\text{B}} = 0.5 \text{ V}$ , $R_{\text{L}} = 1 \text{ k}\Omega$ | 4.9  |      |      | V                |
| Output voltage low-level                     | $V_{\text{OL}}$                            | $V_{\text{CC}} = 5 \text{ V}$ , $V_{\text{B}} = 6 \text{ V}$ , $R_{\text{L}} = 1 \text{ k}\Omega$   |      |      | 0.2  | V                |
| Input resistance                             | $R_{\text{I}}$                             |   | -30% | 47   | +30% | $\text{k}\Omega$ |
| Resistance ratio                             | $R_{\text{I}} / R_{\text{2}}$              |   |      | 2.14 |      | —                |
| Transition frequency                         | $f_{\text{T}}$                             | $V_{\text{CB}} = 10 \text{ V}$ , $I_{\text{E}} = -2 \text{ mA}$ , $f = 200 \text{ MHz}$             |      | 150  |      | MHz              |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

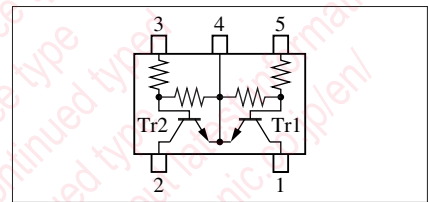
2. \*: Ratio between 2 elements

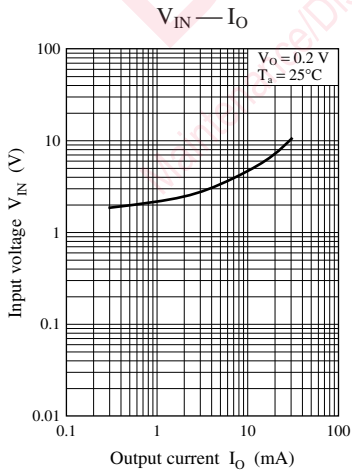
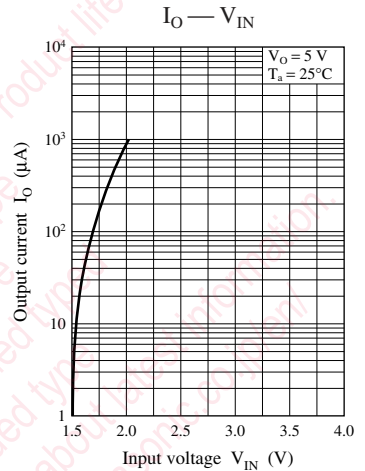
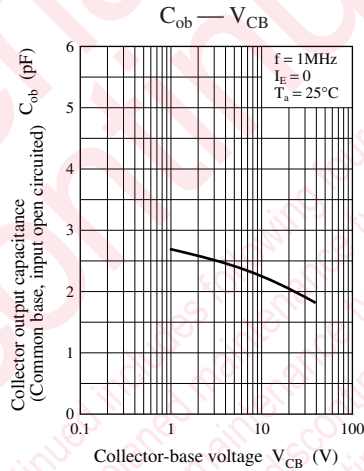
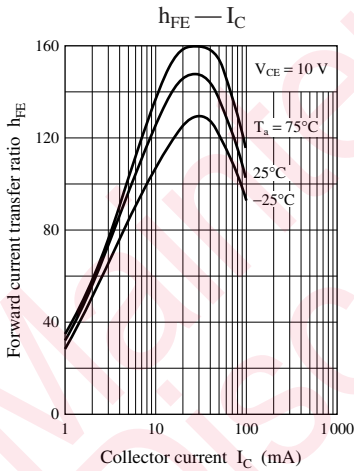
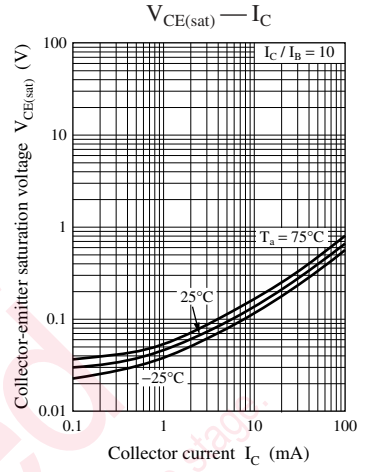
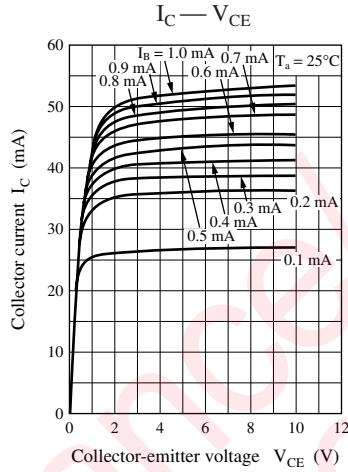
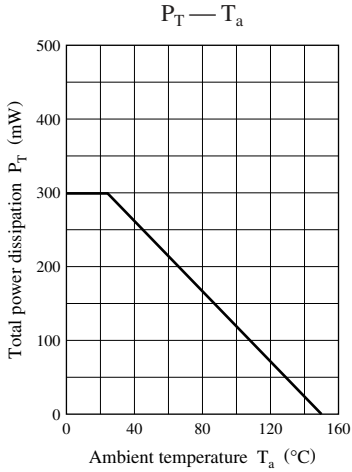
Note) The part number in the parenthesis shows conventional part number.



Marking Symbol: AQ

Internal Connection





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